

isc Silicon NPN RF Transistor

2SC2408

DESCRIPTION

- Low Noise
NF = 2.4 dB TYP. ;@ f = 200 MHz
- High Gain
 $|S_{21e}|^2 = 21$ dB TYP. ;@ f = 200 MHz

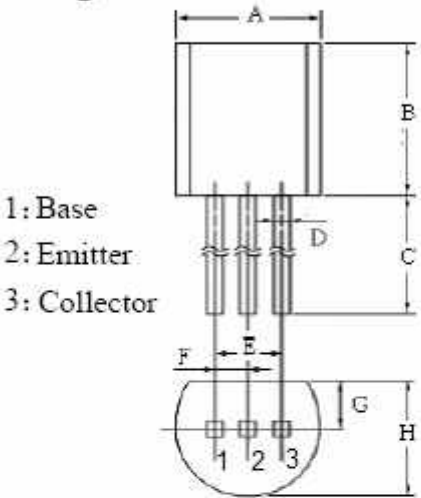
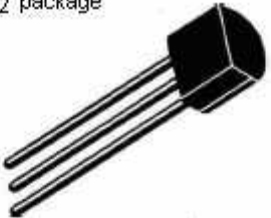
APPLICATIONS

- Designed for use in high frequency wide band amplifier.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	18	V
V_{EBO}	Emitter-Base Voltage	3	V
I_C	Collector Current-Continuous	150	mA
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	0.6	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^{\circ}\text{C}$

TO-92 package



DIM	mm	
	MIN	MAX
A	4.33	4.83
B	4.33	4.83
C	14.0	15.0
D	0.36	0.56
E	2.54	
F	1.27	
G	0.92	1.12
H	3.40	3.60

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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I _{CBO}	Collector Cutoff Current	V _{CB} = 20V; I _E = 0			0.5	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 2V; I _C = 0			0.5	μ A
h _{FE}	DC Current Gain	I _C = 50mA ; V _{CE} = 10V	30		200	
f _T	Current-Gain—Bandwidth Product	I _C = 50mA ; V _{CE} = 10V		3.5		GHz
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = 10V; f= 1.0MHz		1.25	2.0	pF
S _{21e} ²	Insertion Power Gain	I _C = 50mA ; V _{CE} = 10V; f= 200MHz; R _G = 50 Ω	18	21		dB
NF	Noise Figure	I _C = 30mA ; V _{CE} = 10V; f= 200MHz; R _G = 50 Ω		2.4	4.0	dB